

Abstract

The invention concerns a process and an apparatus for the production of gallium nitride or gallium aluminium nitride single crystals. It is essential for the process implementation according to the invention that the vaporisation of gallium or gallium and aluminium is effected at a temperature above the temperature of the growing crystal but at least at 1000°C and that a gas flow comprising nitrogen gas, hydrogen gas, inert gas or a combination of said gases is passed over the surface of the metal melt in such a way that the gas flow over the surface of the metal melt prevents contact of the nitrogen precursor with the metal melt.

Figure 1



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